PNP -1.5A -160V Middle Power Transistor

Parameter	Value
V_{CEO}	-160V
I _C	−1.5A

Features

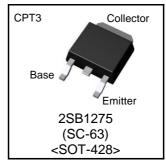
1) Suitable for Middle Power Driver

2) Complementary NPN Types: 2SD1918

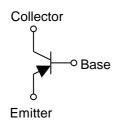
3) High voltage : $V_{CEO} = -160V$

4) Lead Free/RoHS Compliant.

Outline



•Inner circuit



Applications

Motor driver , LED driver Power supply

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SB1275	CPT3	6595	TL	330	16	2,500	B1275

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V _{CBO}	-160	V
Collector-emitter voltage		V _{CEO}	-160	V
Emitter-base voltage		V _{EBO}	-5	V
Collector current	DC	I _C	-1.5	А
	Pulsed	I _{CP} *1	-3.0	Α
Power dissipation		P _D *2	1	W
		P _D *3	10	W
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	-55 to +150	°C

^{*1} Pw=100ms, single pulse

●Electrical characteristics(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV_CEO	$I_C = -1 \text{mA}$	-160	-	-	V
Collector-base breakdown voltage	BV _{CBO}	$I_{C} = -50 \mu A$	-160	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = -50μA	– 5	ı	ı	V
Collector cut-off current	I _{CBO}	V _{CB} = -120V	ı	ı	-1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -4V$	-	-	-1	μΑ
Collector-emitter saturation voltage	V _{CE(sat)} *4	$I_{C} = -1A, I_{B} = -0.1A$	ı	ı	-2	V
DC current gain	h _{FE}	$V_{CE} = -5V, I_{C} = -100 \text{mA}$	82	ı	180	1
Transition frequency	f _T	$V_{CE} = -5V, I_{E} = 100 \text{mA}$ f=30MH _Z	ı	50	-	MHz
Output capacitance	$C_{\sf ob}$	$V_{CB} = -10V, I_{E} = 0A,$ f = 1MHz	ı	30	-	pF

^{*4} Pulsed

●h_{FE} rank categories

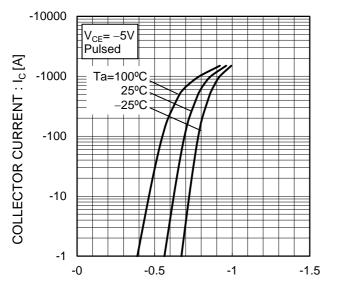
Rank	Р	
h _{FE}	82 to 180	

^{*2} Mounted on a substrate

^{*3} Tc=25°C

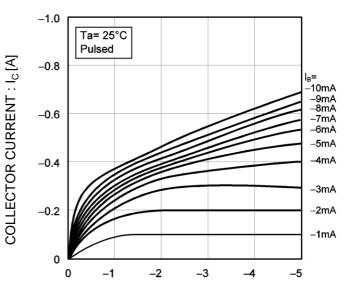
●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics



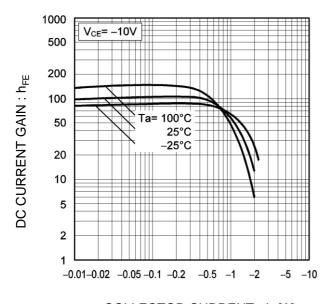
BASE TO EMITTER VOLTAGE : $V_{BE}[V]$

Fig.2 Typical Output Characteristics



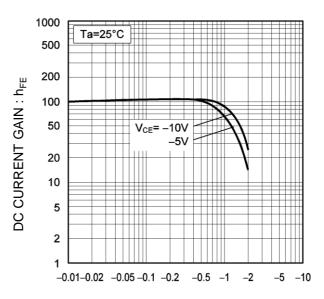
COLECTOR TO EMITTE VOLTAGE : $V_{CE}[V]$

Fig.3 DC Current Gain vs. Collector Current(I)



COLLECTOR CURRENT : I_C[A]

Fig.4 DC current gain vs. output current (II)



COLLECTOR CURRENT : I_C [A]

●Electrical characteristic curves(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage

vs. Collector Current (I) -10 $I_{C}/I_{B}=10$ -5 SATURATION VOLTAGE: V_{CE(sat)} [V] -2 -0.5COLLECTOR-EMITTER -0.2 -0.1 Ta= 100°C -0.0525°C -25°C -0.02-0.01-0.02 -0.05 -0.1 -0.2 -0.5

Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II) Ta=25°C -5 COLLECTOR-EMITTER SATURATION VOLTAGE : V_{CE(sat)} [V] -2 -0.5 -0.2 $I_{C}/I_{B}=50$ -0.120 -0.05-0.02 -0.01 -0.01-0.02 -0.05 -0.1 -0.2 -0.5 -5

COLLECTOR CURRENT : I_C[A]

COLLECTOR CURRENT : $I_C[A]$

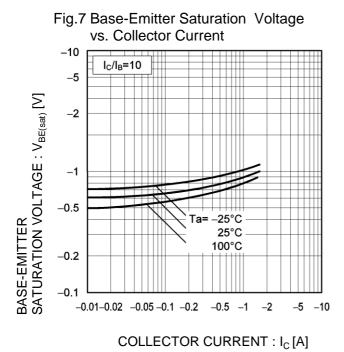


Fig.8 Gain Bandwidth Product vs. Emitter Current 1000 Ta= 25°C 500 V_{CE}= -5V TRANSITION FREQUENCY: fr [MHz] 200 100 50 20 10 5 2 20 50 100 200 500 1000 2 5 10

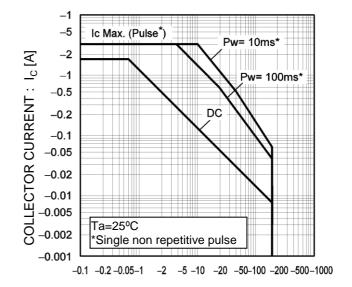
www.rohm.com © 2013 ROHM Co., Ltd. All rights reserved.

EMITTER CURRENT : I_E [mA]

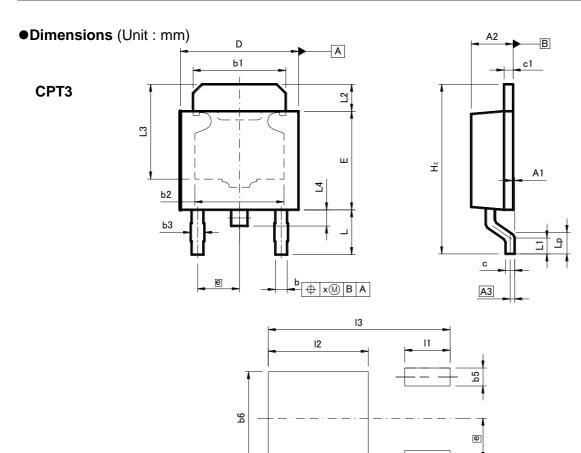
●Electrical characteristic curves(Ta = 25°C)

Fig.9 Collector output capacitance vs. Collector-Base Voltage COLLECTOR OUTPUT CAPACITANCE: Cob [pF] 1000 Ta= 25°C 500 f=1MHz I_E=0A 200 100 50 20 10 5 2 -0.1 -0.2 -0.5 -1 **-5 -10 -20** -50 -100 COLLECTOR - BASE VOLTAGE : V_{CB} [V]

Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE : $V_{CE}[V]$



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.15	0.000	0.006	
A2	2.20	2.50	0.087	0.098	
A3	0.:	25	0.010		
b	0.55	0.75	0.022	0.030	
b1	5.00	5.30	0.197	0.209	
b2	5.0	00	0.1	97	
b3	0.	75	0.0	30	
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.30	6.70	0.248	0.264	
Е	5.40	5.80	0.213	0.228	
е	2.3	30	0.091		
HE	9.00	10.00	0.354	0.394	
L	2.20	2.80	0.087	0.110	
L1	0.80	1.40	0.031	0.055	
L2	1.20	1.80	0.047	0.071	
L3	5.30		0.209		
L4	0.90		0.035		
Lp	1.00	1.60	0.039	0.063	
Х	_	0.25	_	0.010	

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b5	_	1.00	-	0.04	
b6	_	5.20	-	0.205	
l1	_	2.50	_	0.098	
12	_	5.50	-	0.217	
13	-	10.00	-	0.394	

Dimension in mm / inches

Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- 9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor: 2SB1275TLP